Product data sheet

1. General description

NPN/NPN low V_{CEsat} transistor pair in a SOT457 (SC-74) Surface Mounted Device (SMD) plastic package.

PNP/PNP complement: PBSS5160DS

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability: I_C and I_{CM}
- · High collector current gain (hFE) at high IC
- · High efficiency due to less heat generation
- · Smaller required Printed-Circuit Board (PCB) area than for conventional transistors
- AEC-Q101 qualified

3. Applications

- Dual low power switches (e.g. motors, fans)
- · Automotive applications

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit | |
|--------------------|---|--|-----|-----|-----|-----|------|--|
| Per transistor | Per transistor | | | | | | | |
| V _{CEO} | collector-emitter voltage | open base | | - | - | 60 | V | |
| I _C | collector current | | [1] | - | - | 1 | Α | |
| I _{CM} | peak collector current | single pulse; t _p ≤ 1 ms | | - | - | 2 | А | |
| R _{CEsat} | collector-emitter saturation resistance | I_C = 1 A; I_B = 100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C | | - | 200 | 250 | mΩ | |

[1] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



60 V, 1 A NPN/NPN low VCEsat transistor

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|---------------|--------------------|----------------|
| 1 | E1 | emitter TR1 | | C1 B2 E2 |
| 2 | B1 | base TR1 | <u> </u> | |
| 3 | C2 | collector TR2 | | (TR1 TR2) |
| 4 | E2 | emitter TR2 | H1 H2 H3 | |
| 5 | B2 | base TR2 | TSOP6 (SOT457) | |
| 6 | C1 | collector TR1 | | sym020 |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | | | |
|-------------|---------|--|---------|--|--|
| | Name | Description | Version | | |
| PBSS4160DS | TSOP6 | plastic, surface-mounted package (SC-74; TSOP6); 6 leads | SOT457 | | |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PBSS4160DS | B8 |

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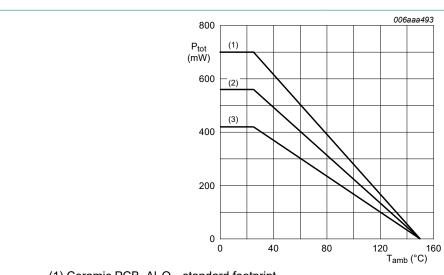
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|------------------|---------------------------|-------------------------------------|-----|-----|------|------|
| Per transist | or | | | | ' | |
| V _{CBO} | collector-base voltage | open emitter | | - | 80 | V |
| V _{CEO} | collector-emitter voltage | open base | | - | 60 | V |
| V _{EBO} | emitter-base voltage | open collector | | - | 5 | V |
| I _C | collector current | | [1] | - | 0.87 | Α |
| | | | [2] | - | 1 | Α |
| | | | [3] | - | 1 | Α |
| I _{CM} | peak collector current | single pulse; t _p ≤ 1 ms | | - | 2 | Α |
| I _B | base current | | | - | 300 | mA |
| I _{BM} | peak base current | single pulse; t _p ≤ 1 ms | | - | 1 | Α |
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C | [1] | - | 290 | mW |
| | | | [2] | - | 370 | mW |
| | | | [3] | - | 450 | mW |
| Per device | | | | | ' | |
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C | [1] | - | 420 | mW |
| | | | [2] | - | 560 | mW |
| | | | [3] | - | 700 | mW |
| Tj | junction temperature | | | - | 150 | °C |
| T _{amb} | ambient temperature | | | -65 | 150 | °C |
| T _{stg} | storage temperature | | | -65 | 150 | °C |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



- (1) Ceramic PCB, Al₂O₃, standard footprint
- (2) FR4 PCB, mounting pad for collector 1 cm²
- (3) FR4 PCB, standard footprint

Fig. 1. Power derating curves

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PBSS4160DS

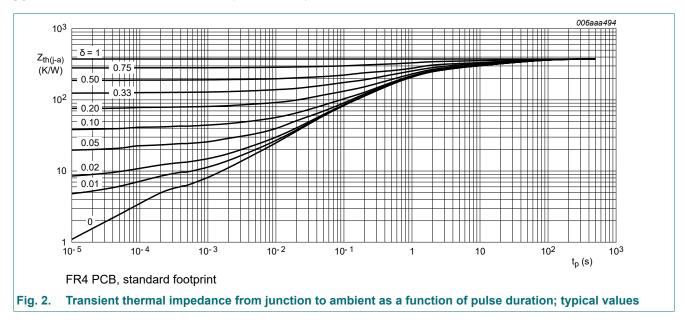
60 V, 1 A NPN/NPN low VCEsat transistor

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|----------------------|--|-------------|-----|-----|-----|-----|------|
| Per transis | tor | | , | | | | |
| ui(j-a) | thermal resistance from | in free air | [1] | - | - | 431 | K/W |
| | junction to ambient | | [2] | - | - | 338 | K/W |
| | | | [3] | - | - | 278 | K/W |
| $R_{th(j-sp)}$ | thermal resistance from junction to solder point | | | - | - | 105 | K/W |
| Per device | ' | | | ' | | ' | |
| R _{th(j-a)} | thermal resistance from | in free air | [1] | - | - | 298 | K/W |
| | junction to ambient | | [2] | - | - | 223 | K/W |
| | | | [3] | - | - | 179 | K/W |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



60 V, 1 A NPN/NPN low VCEsat transistor

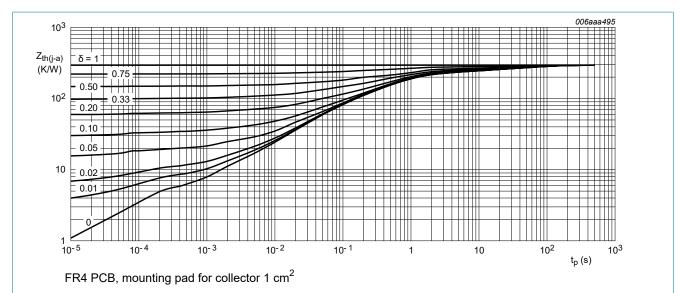


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

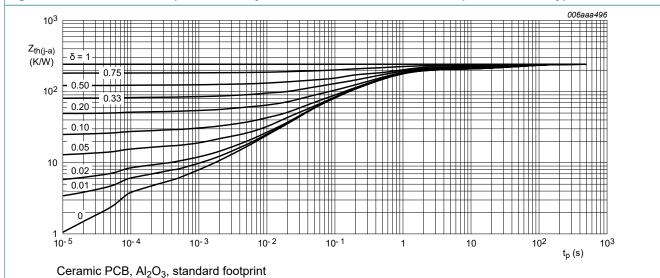


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

60 V, 1 A NPN/NPN low VCEsat transistor

10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|--------------------|---|--|-----|------|-----|------|
| Per transist | tor | | | | | |
| Ісво | collector-base cut-off | V _{CB} = 60 V; I _E = 0 A; T _{amb} = 25 °C | - | - | 100 | nA |
| | current | V _{CB} = 60 V; I _E = 0 A; T _j = 150 °C | - | - | 50 | μΑ |
| I _{EBO} | emitter-base cut-off current | V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C | - | - | 100 | nA |
| I _{CES} | collector-emitter cut-off current | V _{CE} = 60 V; V _{BE} = 0 V; T _{amb} = 25 °C | - | - | 100 | nA |
| h _{FE} | DC current gain | V _{CE} = 5 V; I _C = 1 mA; T _{amb} = 25 °C | 250 | 500 | - | |
| | | V_{CE} = 5 V; I_{C} = 500 mA; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C | 200 | 420 | - | |
| | | V_{CE} = 5 V; I_{C} = 1 A; pulsed; $t_{p} \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C | 100 | 180 | - | |
| V _{CEsat} | collector-emitter | I _C = 100 mA; I _B = 1 mA; T _{amb} = 25 °C | - | 90 | 110 | mV |
| | saturation voltage | I _C = 500 mA; I _B = 50 mA; T _{amb} = 25 °C | - | 115 | 140 | mV |
| | | I_C = 1 A; I_B = 100 mA; pulsed; $t_p \le$ | - | 200 | 250 | mV |
| R _{CEsat} | collector-emitter saturation resistance | 300 μs; δ ≤ 0.02; T _{amb} = 25 °C | - | 200 | 250 | mΩ |
| V _{BEsat} | base-emitter saturation voltage | I_C = 1 A; I_B = 50 mA; pulsed; $t_p \le$ 300 μs; $δ \le 0.02$; T_{amb} = 25 °C | - | 0.95 | 1.1 | V |
| V_{BEon} | base-emitter turn-on voltage | V_{CE} = 5 V; I_{C} = 1 A; pulsed; $t_{p} \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C | - | 0.82 | 0.9 | V |
| t _d | delay time | I _C = 0.5 A; I _{Bon} = 25 mA; I _{Boff} = -25 mA; | - | 11 | - | ns |
| t _r | rise time | T _{amb} = 25 °C | - | 78 | - | ns |
| t _{on} | turn-on time | | - | 90 | - | ns |
| t _s | storage time | | - | 340 | - | ns |
| t _f | fall time | | - | 160 | - | ns |
| t _{off} | turn-off time | | - | 500 | - | ns |
| f _T | transition frequency | V_{CE} = 10 V; I_{C} = 50 mA; f = 100 MHz; T_{amb} = 25 °C | 150 | 220 | - | MHz |
| C _c | collector capacitance | $V_{CB} = 10 \text{ V}; I_{E} = 0 \text{ A}; i_{e} = 0 \text{ A}; f = 1 \text{ MHz}; $ $T_{amb} = 25 ^{\circ}\text{C}$ | - | 5.5 | 10 | pF |

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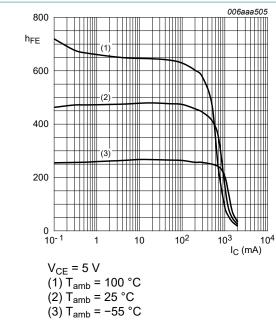
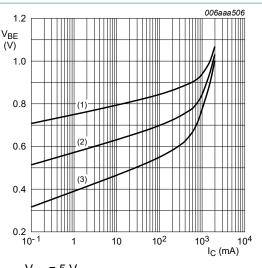
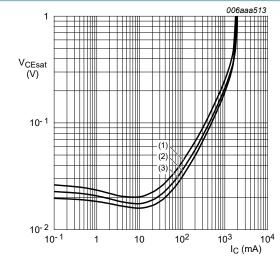


Fig. 5. DC current gain as a function of collector current; typical values



 $V_{CE} = 5 \text{ V}$ (1) $T_{amb} = -55 \text{ °C}$ (2) $T_{amb} = 25 \text{ °C}$ (3) $T_{amb} = 100 \text{ °C}$

Fig. 6. Base-emitter voltage as a function of collector current; typical values



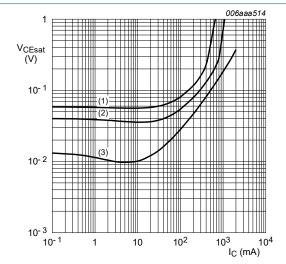
 $I_{\rm C}/I_{\rm B}=20$

(1) T_{amb} = 100 °C

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values



T_{amb} = 25 °C

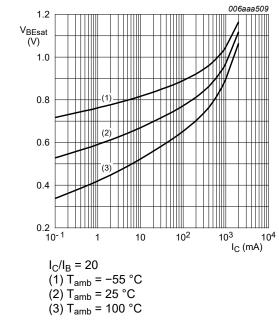
(1) $I_C/I_B = 100$

(2) $I_C/I_B = 50$

(3) $I_C/I_B = 10$

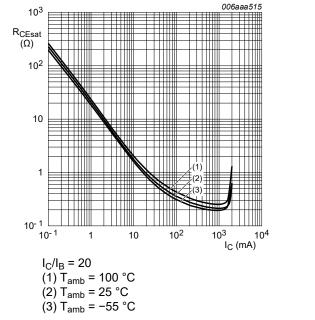
Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

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(2)
$$T_{amb} = 25 \, ^{\circ}C$$

Fig. 9. collector current; typical values



Base-emitter saturation voltage as a function of Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

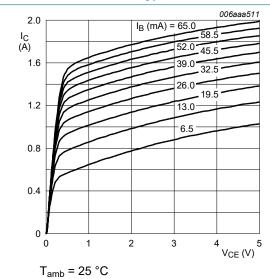
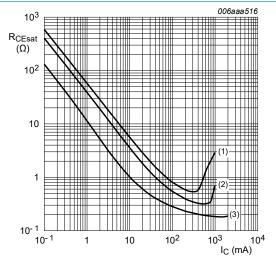


Fig. 11. Collector current as a function of collectoremitter voltage; typical values



$$T_{amb} = 25 \, ^{\circ}C$$

(1) $I_{C}/I_{B} = 100$

(2) $I_{\rm C}/I_{\rm B} = 50$

(3) $I_C/I_B = 10$

Fig. 12. Collector-emitter saturation resistance as a function of collector current; typical values

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11. Test information

Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

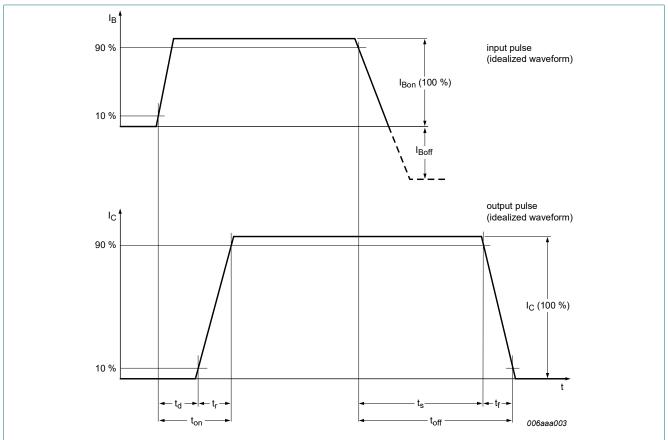
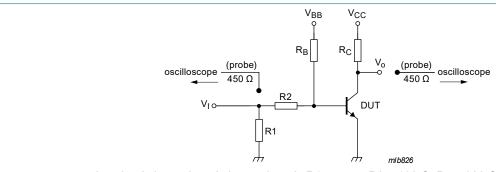


Fig. 13. Transistor switching time definition

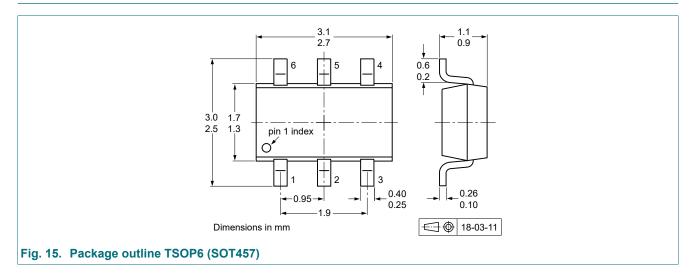


 I_C = 0.5 A; I_{Bon} = 25 mA; I_{Boff} = -25 mA; R1 = open; R2 = 100 Ω ; R_B = 300 Ω ; R_C = 20 Ω

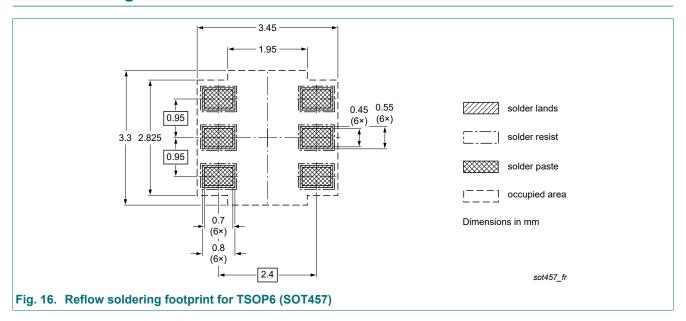
Fig. 14. Test circuit for switching times

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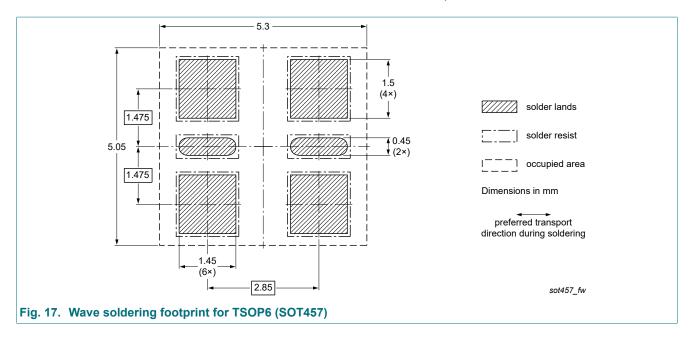
12. Package outline



13. Soldering



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14. Revision history

Table 8. Revision history

| Tuble 6. Nevision history | | | | | | |
|---------------------------|----------------------------|--|---------------|--------------|--|--|
| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes | | |
| PBSS4160DS v.5 | 20230921 | Product data sheet | - | PBSS4160DS_4 | | |
| Modifications: | Nexperia. • Legal texts ha | this data sheet has been rederve been adapted to the new coing information" removed. | | , , | | |
| PBSS4160DS_4 | 20091211 | Product data sheet | - | PBSS4160DS_3 | | |
| PBSS4160DS_3 | 20060209 | Product data sheet | - | PBSS4160DS_2 | | |
| PBSS4160DS_2 | 20050627 | Product data sheet | - | PBSS4160DS_1 | | |
| PBSS4160DS_1 | 20040426 | Objective data sheet | - | - | | |

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15. Legal information

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| Document status [1][2] | Product status [3] | Definition |
|--------------------------------|-----------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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